VS-HFA04TB60S-M3

Vishay Semiconductors

HEXFRED[®], Ultrafast Soft Recovery Diode, 4 A



www.vishay.com

| PRIMARY CHARACTERISTICS | | | | | | |
|----------------------------------|-------------------------------|--|--|--|--|--|
| I _{F(AV)} 4 A | | | | | | |
| V _R | 600 V | | | | | |
| V _F at I _F | 1.4 V | | | | | |
| t _{rr} (typ.) | 17 ns | | | | | |
| T _J max. | 150 °C | | | | | |
| Package | D ² PAK (TO-263AB) | | | | | |
| Circuit configuration | Single | | | | | |

FEATURES

- Ultrafast recovery
- Ultrasoft recovery
- Very low I_{RRM}
- Very low Q_{rr}
- Specified at operating temperature
- Meets MSL level 1, per J-STD-020, LF maximum peak of 245 °C
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

BENEFITS

- Reduced RFI and EMI
- Reduced power loss in diode and switching transistor
- Higher frequency operation
- Reduced snubbing
- · Reduced parts count

DESCRIPTION

VS-HFA04TB60S is a state of the art ultrafast recovery diode. Employing the latest in epitaxial construction and advanced processing techniques it features a superb combination of characteristics which result in performance which is unsurpassed by any rectifier previously available. With basic ratings of 600 V and 4 A continuous current, the VS-HFA04TB60S is especially well suited for use as the companion diode for IGBTs and MOSFETs. In addition to ultrafast recovery time, the HEXFRED® product line features extremely low values of peak recovery current (I_{RBM}) and does not exhibit any tendency to "snap-off" during the tb portion of recovery. The HEXFRED features combine to offer designers a rectifier with lower noise and significantly lower switching losses in both the diode and the switching transistor. These HEXFRED advantages can help to significantly reduce snubbing, component count and heatsink sizes. The HEXFRED VS-HFA04TB60S is ideally suited for applications in power supplies and power conversion systems (such as inverters), motor drives, and many other similar applications where high speed, high efficiency is needed.

| ABSOLUTE MAXIMUM RATINGS | | | | | | | |
|--|-----------------------------------|-------------------------|-------------|-------|--|--|--|
| PARAMETER | SYMBOL | TEST CONDITIONS | VALUES | UNITS | | | |
| Cathode to anode voltage | V _R | | 600 | V | | | |
| Maximum continuous forward current | I _F | T _C = 100 °C | 4 | | | | |
| Single pulse forward current | I _{FSM} | | 25 | А | | | |
| Maximum repetitive forward current | I _{FRM} | | 16 | | | | |
| Maximum power dissipation | PD | T _C = 25 °C | 25 | W | | | |
| Maximum power dissipation | | T _C = 100 °C | 10 | vv | | | |
| Operating junction and storage temperature range | T _J , T _{Stg} | | -55 to +150 | °C | | | |

Revision: 16-Dec-2021

1

Document Number: 96215

For technical questions within your region: <u>DiodesAmericas@vishay.com</u>, <u>DiodesAsia@vishay.com</u>, <u>DiodesEuropa@vishay.com</u> THIS DOCUMENT IS SUBJECT TO CHANGE WITHOUT NOTICE. THE PRODUCTS DESCRIBED HEREIN AND THIS DOCUMENT ARE SUBJECT TO SPECIFIC DISCLAIMERS, SET FORTH AT <u>www.vishay.com/doc?91000</u>



FREE



www.vishay.com

Vishay Semiconductors

| ELECTRICAL SPECIFICATIONS (T _J = 25 °C unless otherwise specified) | | | | | | | | |
|--|-----------------|--|------------|------|------|------|-------|--|
| PARAMETER | SYMBOL | TEST CONDITIONS | | MIN. | TYP. | MAX. | UNITS | |
| Cathode to anode breakdown voltage | V_{BR} | I _R = 100 μA | | 600 | - | - | | |
| | | I _F = 4.0 A | See fig. 1 | - | 1.5 | 1.8 | v | |
| Maximum forward voltage | V _{FM} | I _F = 8.0 A | | - | 1.8 | 2.2 | | |
| | | I _F = 4.0 A, T _J = 125 °C | | - | 1.4 | 1.7 | | |
| Maximum reverse leakage current | 1 | $V_R = V_R$ rated | See fig. 2 | - | 0.17 | 3.0 | | |
| Maximum reverse leakage current | I _{RM} | $T_J = 125 \text{ °C}, V_R = 0.8 \text{ x } V_R \text{ rated}$ | See fig. 2 | - | 44 | 300 | μA | |
| Junction capacitance | CT | V _R = 200 V | See fig. 3 | - | 4.0 | 8.0 | pF | |
| Series inductance | L _S | Measured lead to lead 5 mm from package body - | | 8.0 | - | nH | | |

| DYNAMIC RECOVERY CHARACTERISTICS (T _J = 25 °C unless otherwise specified) | | | | | | | | |
|---|---------------------------|---|--|------|------|------|-------|--|
| PARAMETER | SYMBOL | TEST CON | IDITIONS | MIN. | TYP. | MAX. | UNITS | |
| | t _{rr} | $I_F = 1.0 \text{ A}, \text{ d}I_F/\text{d}t = 200 \text{ A}$ | õs, V _R = 30 V | - | 17 | - | | |
| Reverse recovery time See fig. 5, 6 | t _{rr1} | T _J = 25 °C | | - | 28 | 42 | ns | |
| | t _{rr2} | T _J = 125 °C | I _F = 4.0 A di _F /dt = 200 A/μs | - | 38 | 57 | T I | |
| Peak recovery current | I _{RRM1} | T _J = 25 °C | | - | 2.9 | 5.2 | A | |
| Feat recovery current | I _{RRM2} | T _J = 125 °C | | - | 3.7 | 6.7 | ~ | |
| Reverse recovery charge | Q _{rr1} | T _J = 25 °C | $V_{\rm B} = 200 \text{ V}$ | - | 40 | 60 | nC | |
| See fig. 7 | Q _{rr2} | T _J = 125 °C | | - | 70 | 105 | 110 | |
| Peak rate of fall of recovery current | di _{(rec)M} /dt1 | T _J = 25 °C | | - | 280 | - | A∕µs | |
| during t _b , see fig. 8 | di _{(rec)M} /dt2 | T _J = 125 °C | | - | 235 | - | γvµs | |

| THERMAL - MECHANICAL SPECIFICATIONS | | | | | | | | |
|---|-------------------|--|------|-------|-------|--------|--|--|
| PARAMETER | SYMBOL | TEST CONDITIONS | MIN. | TYP. | MAX. | UNITS | | |
| Lead temperature | T _{lead} | 0.063" from case (1.6 mm) for 10 s | - | - | 300 | °C | | |
| Thermal resistance, junction-to-case | R _{thJC} | | - | - | 5.0 | K/W | | |
| Thermal resistance, junction-to-ambient | R _{thJA} | Typical socket mount | - | - | 80 | r\/ vv | | |
| Woisht | | | - | 2.0 | - | g | | |
| Weight | | | - | 0.07 | - | oz. | | |
| Marking device | | Case style D ² PAK (TO-263AB) | | HFA04 | TB60S | | | |



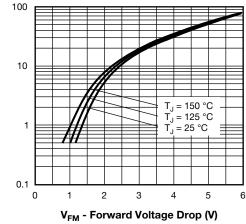


Fig. 1 - Maximum Forward Voltage Drop vs. Instantaneous Forward Current

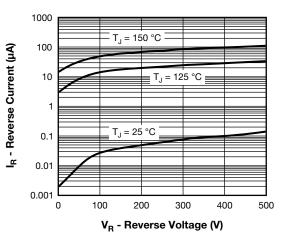


Fig. 2 - Typical Reverse Current vs. Reverse Voltage

Revision: 16-Dec-2021

2

Document Number: 96215

For technical questions within your region: <u>DiodesAmericas@vishay.com</u>, <u>DiodesAsia@vishay.com</u>, <u>DiodesEuropa@vishay.com</u> THIS DOCUMENT IS SUBJECT TO CHANGE WITHOUT NOTICE. THE PRODUCTS DESCRIBED HEREIN AND THIS DOCUMENT ARE SUBJECT TO SPECIFIC DISCLAIMERS, SET FORTH AT <u>www.vishay.com/doc?91000</u>



Vishay Semiconductors

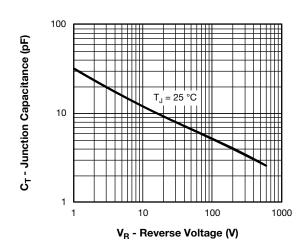


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

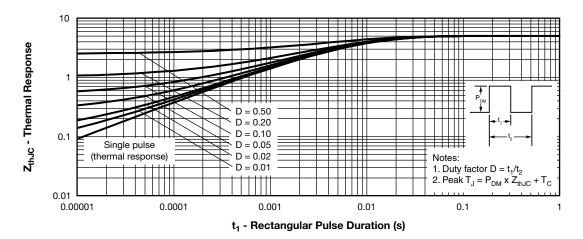


Fig. 4 - Maximum Thermal Impedance Z_{thJC} Characteristics

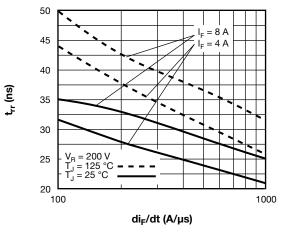


Fig. 5 - Typical Reverse Recovery Time vs. $di_{\mbox{\scriptsize F}}/dt$

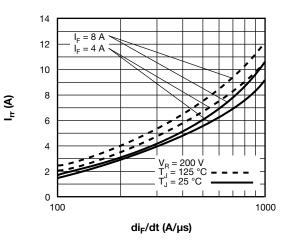


Fig. 6 - Typical Recovery Current vs. di_F/dt

Revision: 16-Dec-2021

SHAY

www.vishay.com

3

Document Number: 96215

For technical questions within your region: <u>DiodesAmericas@vishay.com</u>, <u>DiodesAsia@vishay.com</u>, <u>DiodesEuropa@vishay.com</u> THIS DOCUMENT IS SUBJECT TO CHANGE WITHOUT NOTICE. THE PRODUCTS DESCRIBED HEREIN AND THIS DOCUMENT ARE SUBJECT TO SPECIFIC DISCLAIMERS, SET FORTH AT <u>www.vishay.com/doc?91000</u>

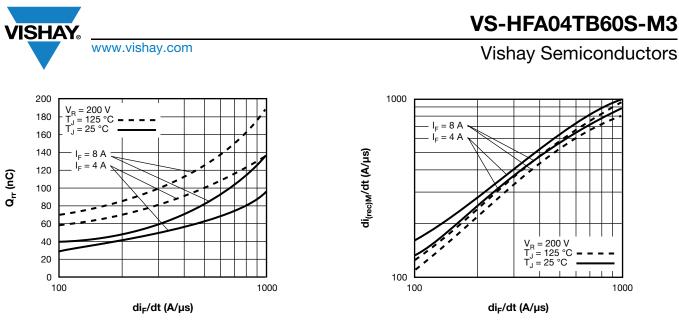


Fig. 7 - Typical Stored Charge vs. di_F/dt



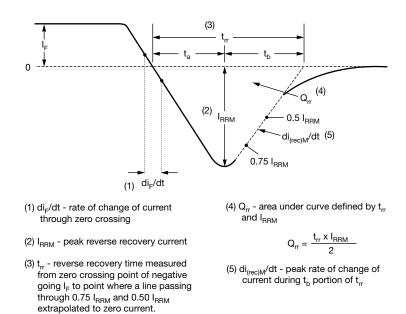


Fig. 9 - Reverse Recovery Waveform and Definitions

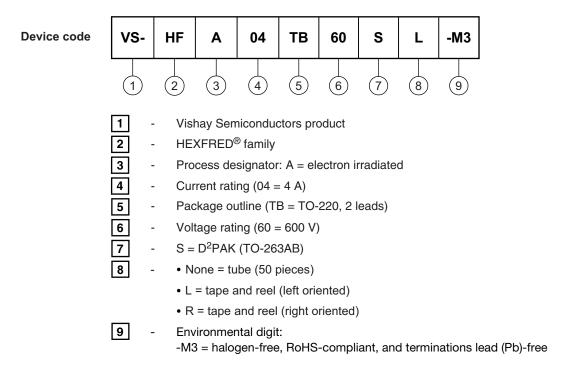
VS-HFA04TB60S-M3

Vishay Semiconductors

ORDERING INFORMATION TABLE

www.vishay.com

SHAY



| ORDERING INFORMATION (Example) | | | | | | | |
|---|-----|-------------------------|--|--|--|--|--|
| PREFERRED P/N BASE QUANTITY PACKAGING DESCRIPTION | | | | | | | |
| VS-HFA04TB60S-M3 | 50 | Antistatic plastic tube | | | | | |
| VS-HFA04TB60SL-M3 | 800 | 13" diameter reel | | | | | |
| VS-HFA04TB60SR-M3 | 800 | 13" diameter reel | | | | | |

| LINKS TO RELATED DOCUMENTS | | | | | |
|-------------------------------------|--------------------------|--|--|--|--|
| Dimensions www.vishay.com/doc?96164 | | | | | |
| Part marking information | www.vishay.com/doc?95444 | | | | |
| Packaging information | www.vishay.com/doc?96424 | | | | |

Vishay Semiconductors

D²PAK

DIMENSIONS in millimeters and inches



| ota | ted | 90 | °C |
|----------|------|-------------|----|
| <u>S</u> | cale | <u>ə:</u> 8 | :1 |

| SYMBOL | MILLIM | ETERS | INCHES | | NOTES | |
|--------|--------|-------|--------|-------|-------|--|
| STMBOL | MIN. | MAX. | MIN. | MAX. | NOTES | |
| А | 4.06 | 4.83 | 0.160 | 0.190 | | |
| A1 | 0.00 | 0.254 | 0.000 | 0.010 | | |
| b | 0.51 | 0.99 | 0.020 | 0.039 | | |
| b1 | 0.51 | 0.89 | 0.020 | 0.035 | 4 | |
| b2 | 1.14 | 1.78 | 0.045 | 0.070 | | |
| b3 | 1.14 | 1.73 | 0.045 | 0.068 | 4 | |
| с | 0.38 | 0.74 | 0.015 | 0.029 | | |
| c1 | 0.38 | 0.58 | 0.015 | 0.023 | 4 | |
| c2 | 1.14 | 1.65 | 0.045 | 0.065 | | |
| D | 8.51 | 9.65 | 0.335 | 0.380 | 2 | |

| SYMBOL | | MILLIM | ETERS | INCHES | | NOTES |
|--------|--------|----------|-------|-----------|-------|-------|
| | STNDUL | MIN. | MAX. | MIN. | MAX. | NOTES |
| | D1 | 6.86 | 8.00 | 0.270 | 0.315 | 3 |
| | E | 9.65 | 10.67 | 0.380 | 0.420 | 2, 3 |
| | E1 | 7.90 | 8.80 | 0.311 | 0.346 | 3 |
| | е | 2.54 BSC | | 0.100 BSC | | |
| | Н | 14.61 | 15.88 | 0.575 | 0.625 | |
| | L | 1.78 | 2.79 | 0.070 | 0.110 | |
| | L1 | - | 1.65 | - | 0.066 | 3 |
| | L2 | 1.27 | 1.78 | 0.050 | 0.070 | |
| | L3 | 0.25 BSC | | 0.010 | BSC | |
| | L4 | 4.78 | 5.28 | 0.188 | 0.208 | |

Notes

⁽¹⁾ Dimensioning and tolerancing per ASME Y14.5 M-1994

(2) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outmost extremes of the plastic body

(3) Thermal pad contour optional within dimension E, L1, D1 and E1

⁽⁴⁾ Dimension b1 and c1 apply to base metal only

(5) Datum A and B to be determined at datum plane H

(6) Controlling dimension: inches

⁽⁷⁾ Outline conforms to JEDEC[®] outline TO-263AB

Revision: 13-Jul-17

1

Document Number: 96164

For technical questions within your region: DiodesAmericas@vishav.com, DiodesAsia@vishav.com, DiodesEurope@vishav.com THIS DOCUMENT IS SUBJECT TO CHANGE WITHOUT NOTICE. THE PRODUCTS DESCRIBED HEREIN AND THIS DOCUMENT ARE SUBJECT TO SPECIFIC DISCLAIMERS, SET FORTH AT www.vishav.com/doc?91000





Vishay

Disclaimer

ALL PRODUCT, PRODUCT SPECIFICATIONS AND DATA ARE SUBJECT TO CHANGE WITHOUT NOTICE TO IMPROVE RELIABILITY, FUNCTION OR DESIGN OR OTHERWISE.

Vishay Intertechnology, Inc., its affiliates, agents, and employees, and all persons acting on its or their behalf (collectively, "Vishay"), disclaim any and all liability for any errors, inaccuracies or incompleteness contained in any datasheet or in any other disclosure relating to any product.

Vishay makes no warranty, representation or guarantee regarding the suitability of the products for any particular purpose or the continuing production of any product. To the maximum extent permitted by applicable law, Vishay disclaims (i) any and all liability arising out of the application or use of any product, (ii) any and all liability, including without limitation special, consequential or incidental damages, and (iii) any and all implied warranties, including warranties of fitness for particular purpose, non-infringement and merchantability.

Statements regarding the suitability of products for certain types of applications are based on Vishay's knowledge of typical requirements that are often placed on Vishay products in generic applications. Such statements are not binding statements about the suitability of products for a particular application. It is the customer's responsibility to validate that a particular product with the properties described in the product specification is suitable for use in a particular application. Parameters provided in datasheets and / or specifications may vary in different applications and performance may vary over time. All operating parameters, including typical parameters, must be validated for each customer application by the customer's technical experts. Product specifications do not expand or otherwise modify Vishay's terms and conditions of purchase, including but not limited to the warranty expressed therein.

Hyperlinks included in this datasheet may direct users to third-party websites. These links are provided as a convenience and for informational purposes only. Inclusion of these hyperlinks does not constitute an endorsement or an approval by Vishay of any of the products, services or opinions of the corporation, organization or individual associated with the third-party website. Vishay disclaims any and all liability and bears no responsibility for the accuracy, legality or content of the third-party website or for that of subsequent links.

Vishay products are not designed for use in life-saving or life-sustaining applications or any application in which the failure of the Vishay product could result in personal injury or death unless specifically qualified in writing by Vishay. Customers using or selling Vishay products not expressly indicated for use in such applications do so at their own risk. Please contact authorized Vishay personnel to obtain written terms and conditions regarding products designed for such applications.

No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted by this document or by any conduct of Vishay. Product names and markings noted herein may be trademarks of their respective owners.

© 2024 VISHAY INTERTECHNOLOGY, INC. ALL RIGHTS RESERVED

Revision: 01-Jul-2024